

BLC6G20-110; BLC6G20LS-110

UHF power LDMOS transistor

Rev. 01 — 30 January 2006

Objective data sheet

1. Product profile

1.1 General description

110 W LDMOS power transistor for base station applications at frequencies from 1800 MHz to 2000 MHz.

Table 1: Typical performance

RF performance at $T_{case} = 25^{\circ}C$ in a common source class-AB production test circuit.

Mode of operation	f (MHz)	V _{DS} (V)	P _L (W)	G _p (dB)	η_D (%)	ACPR ₄₀₀ (dBc)	ACPR ₆₀₀ (dBc)	EVM (%)	IMD3 (dBc)	ACPR (dBc)
CW	1930 to 1990	28	100	17	51	-	-	-	-	-
GSM EDGE	1930 to 1990	28	48 (AV)	17.5	40	-60	-70	2.1	-	-
2-carrier W-CDMA	1930 to 1990	28	25 (AV)	18	32	-	-	-	-37 [1]	-40 [1]

[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7 dB at 0.01 % probability on CCDF per carrier; carrier spacing 10 MHz.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- Typical 2-carrier W-CDMA performance at frequencies of 1930 MHz and 1990 MHz, a supply voltage of 28 V and an I_{Dq} of 950 mA:
 - ◆ Output power = 25 W (AV)
 - ◆ Gain = 18 dB
 - ◆ Efficiency = 32 %
 - ◆ IMD3 = -37 dBc
 - ◆ ACPR = -40 dBc
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1800 MHz to 2000 MHz)
- Internally matched for ease of use

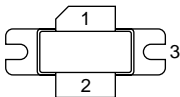
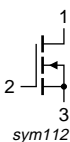
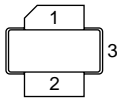
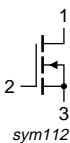
PHILIPS

1.3 Applications

- RF power amplifiers for GSM, GSM EDGE, W-CDMA and CDMA base stations and multi carrier applications in the 1800 MHz to 2000 MHz frequency range.

2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
BLC6G20-110 (SOT895-1)			
1	drain		 sym112
2	gate		
3	source		
BLC6G20LS-110 (SOT896-1)			
1	drain		 sym112
2	gate		
3	source		

[1] Connected to flange

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
BLC6G20-110	-	plastic flanged cavity package; 2 mounting slots; 2 leads	SOT895-1
BLC6G20LS-110	-	plastic earless flanged cavity package; 2 leads	SOT896-1

4. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
I_D	drain current		-	<td>	A
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	225	°C

5. Thermal characteristics

Table 5: Thermal characteristics

Symbol	Parameter	Conditions	Type	Min	Typ	Max	Unit
$R_{th(j-case)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C};$ $P_L = 25\text{ W}$	BLC6G20-110	<tbid>	<tbid>	<tbid>	K/W
			BLC6G20LS-110	<tbid>	0.45	0.54	K/W

6. Characteristics

Table 6: Characteristics

$T_j = 25\text{ °C}$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.5\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 150\text{ mA}$	<tbid>	2	<tbid>	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28\text{ V}; I_D = 950\text{ mA}$	<tbid>	<tbid>	<tbid>	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V}$	-	-	5	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $V_{DS} = 10\text{ V}$	23	27	-	A
I_{GSS}	gate leakage current	$V_{GS} = 13\text{ V}; V_{DS} = 0\text{ V}$	-	-	450	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 7.5\text{ A}$	-	10.5	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $I_D = 5.25\text{ A}$	-	0.1	0.125	Ω
C_{rs}	feedback capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V};$ $f = 1\text{ MHz}$	-	<tbid>	-	pF

7. Application information

Table 7: Application information

Mode of operation: 2-carrier W-CDMA; PAR 7 dB at 0.01 % probability on CCDF; 3GPP test model 1; 1-64 PDPCH; $f_1 = 1932.5\text{ MHz}; f_2 = 1942.5\text{ MHz}; f_3 = 1977.5\text{ MHz}; f_4 = 1987.5\text{ MHz};$ RF performance at $V_{DS} = 28\text{ V}; I_{Dq} = 950\text{ mA}; T_{case} = 25\text{ °C};$ unless otherwise specified; in a class-AB production test circuit

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(AV)}$	average output power		-	25	-	W
G_p	power gain	$P_{L(AV)} = 25\text{ W}$	-	18	-	dB
η_D	drain efficiency	$P_{L(AV)} = 25\text{ W}$	-	32	-	%
IMD3	third order intermodulation distortion	$P_{L(AV)} = 25\text{ W}$	-	-37	-	dBc
ACPR	adjacent channel power ratio	$P_{L(AV)} = 25\text{ W}$	-	-40	-	dBc

7.1 Ruggedness in class-AB operation

The BLC6G20-110 and BLC6G20LS-110 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:

$V_{DS} = 28\text{ V}; I_{Dq} = 950\text{ mA}; P_L = 110\text{ W (CW)}; f = 1990\text{ MHz}.$

8. Package outline

Plastic flanged cavity package; 2 mounting slots; 2 leads

SOT895-1

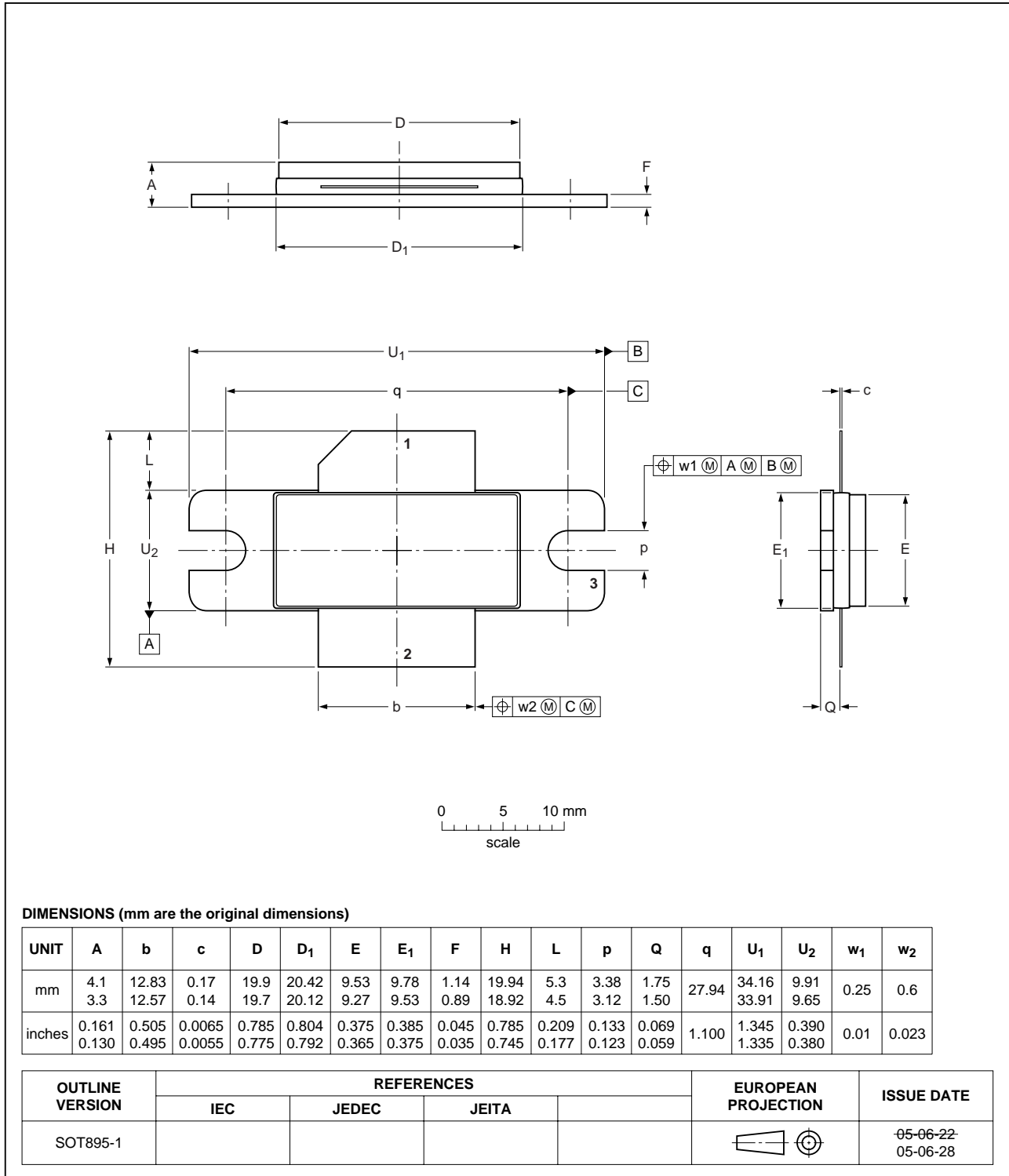


Fig 1. Package outline SOT895-1

Plastic earless flanged cavity package; 2 leads

SOT896-1

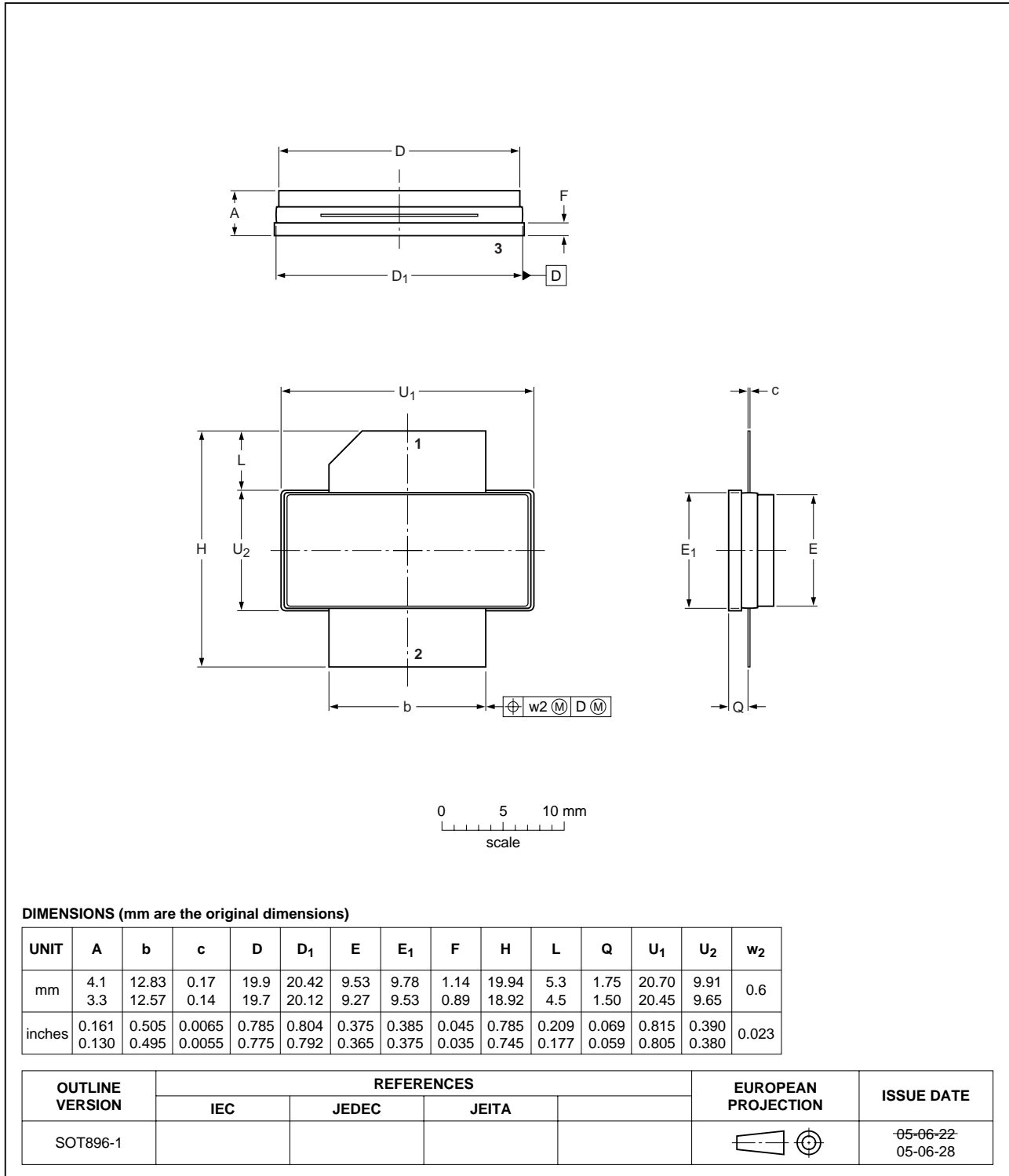


Fig 2. Package outline SOT896-1

9. Abbreviations

Table 8: Abbreviations

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CDMA	Code Division Multiple Access
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
EDGE	Enhanced Data rates for GSM Evolution
EVM	Error Vector Magnitude
GSM	Global System for Mobile communications
LDMOS	Laterally Diffused Metal Oxide Semiconductor
PAR	Peak-to-Average power Ratio
PDPCH	transmission Power of the Dedicated Physical CHannel
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

10. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BLC6G20-110_6G20 LS-110_1	20060130	Objective data sheet	-	-	-

11. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

12. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

13. Disclaimers

Life support — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors

15. Contact information

For additional information, please visit: <http://www.semiconductors.philips.com>

For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com

customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

14. Trademarks

Notice — All referenced brands, product names, service names and trademarks are the property of their respective owners.

16. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	2
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	3
6	Characteristics	3
7	Application information	3
7.1	Ruggedness in class-AB operation	3
8	Package outline	4
9	Abbreviations	6
10	Revision history	7
11	Data sheet status	8
12	Definitions	8
13	Disclaimers	8
14	Trademarks	8
15	Contact information	8



© Koninklijke Philips Electronics N.V. 2006

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Date of release: 30 January 2006

Document number: BLC6G20-110_6G20LS-110_1

Published in The Netherlands